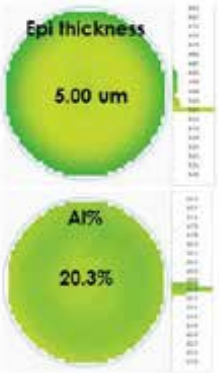
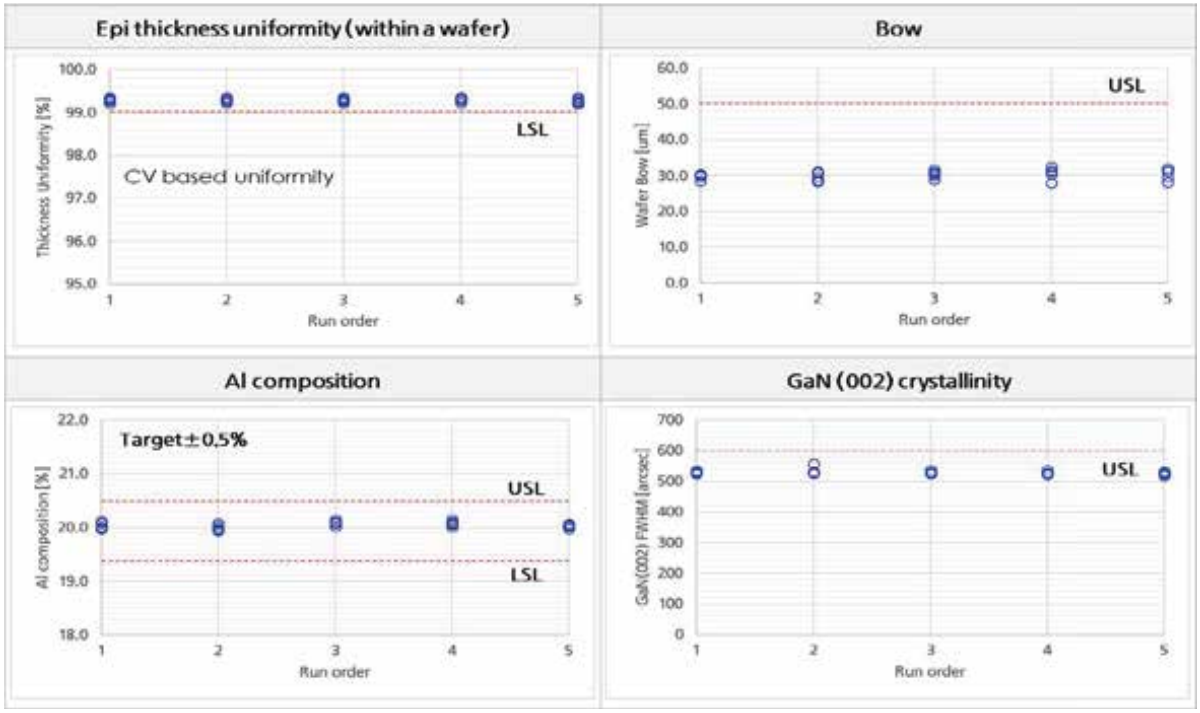
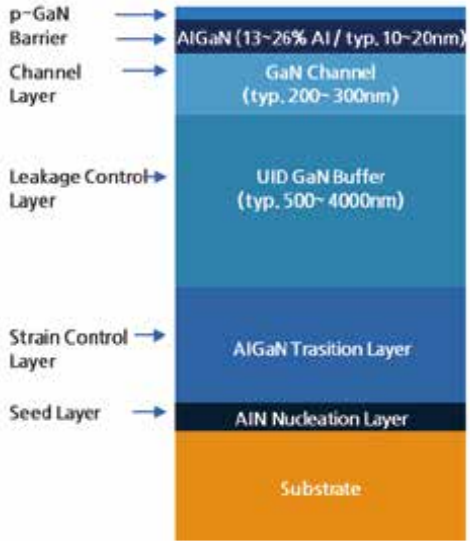
8 inch GaN on Si Epiwafer Production Capacity

Uniformity Control

Thickness uniformity	Surface roughness	Wafer bow	Al% uniformity	Edge crack	Crystal quality
0.8 % (5um)	1 nm	±50 um	0.6 %	1.0 mm	540/750







Aixtron G10, 8" GaN on Si (6PM)



OSTECH

os_inquiry@ostech.co.jp http://www.ostech.co.jp

〒590-0023 大阪府堺市堺区南三国ケ丘町 5-2-27
TEL : 072-221-2778 FAX : 072-221-2779